Product data sheet

1. General description

NPN low V_{CEsat} transistor in a SOT89 (SC-62/TO-243) small and flat lead Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS5540X-Q

2. Features and benefits

- High h_{FE} and low V_{CEsat} at high current operation
- High collector current capability: I_C maximum 4 A
- High efficiency leading to less heat generation
- Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- Medium power peripheral drivers (e.g. fan and motor)
- · Strobe flash units for DSC and mobile phones
- Inverter applications (e.g. TFT displays)
- · Power switch for LAN and ADSL systems
- Medium power DC-to-DC conversion
- Battery chargers

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	40	V
I _C	collector current		-	-	4	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 10 ms	-	-	10	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 5 A; I_B = 500 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	40	71	mΩ

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		С
2	С	collector		
3	В	base	3 2 1	B — ,
			SOT89	sym123



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6. Ordering information

Table 3. Ordering information

Type number			
	Name	Description	Version
PBSS4540X-Q		plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	<u>SOT89</u>

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS4540X-Q	%1B

[1] % = placeholder for manufacturing site code

8. Limiting values

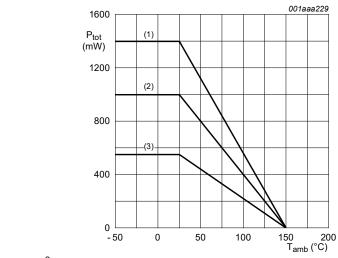
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	40	V
V_{CEO}	collector-emitter voltage	open base		-	40	V
V _{EBO}	emitter-base voltage	open collector		-	6	V
I _C	collector current			-	4	Α
I _{CRM}	repetitive peak collector current	$\delta \le 0.02; t_p \le 10 \text{ ms}$	[1]	-	5	A
I _{CM}	peak collector current	single pulse; t _p ≤ 10 ms		-	10	Α
I _B	base current			-	1	Α
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	2	A
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1] [2]	-	2.5	W
			[1]	-	0.55	W
			[3]	-	1	W
			[4]	-	1.4	W
			[5]	-	1.6	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Operated under pulsed conditions; $t_p \le 10$ ms; $\delta \le 0.2$.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm². Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm². Device mounted on a 7 cm² ceramic PCB, 1 cm² single-sided copper and tin-plated. [3]

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- (1) FR4 PCB; 6 cm² mounting pad for collector (2) FR4 PCB; 1 cm² mounting pad for collector
- (3) FR4; standard footprint

Power derating curves Fig. 1.

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air [1] [2] [1] [3] [4] [5]	[1] [2]	-	-	50	K/W
	junction to ambient		[1]	-	-	225	K/W
			[3]	-	-	125	K/W
			[4]	-	-	90	K/W
			-	-	80	K/W	
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	16	K/W

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Operated under pulsed conditions; $t_p \le 10$ ms; $\delta \le 0.2$. Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm². Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm². [3]
- [4]
- Device mounted on a 7 cm² ceramic PCB, 1 cm² single-sided copper and tin-plated.

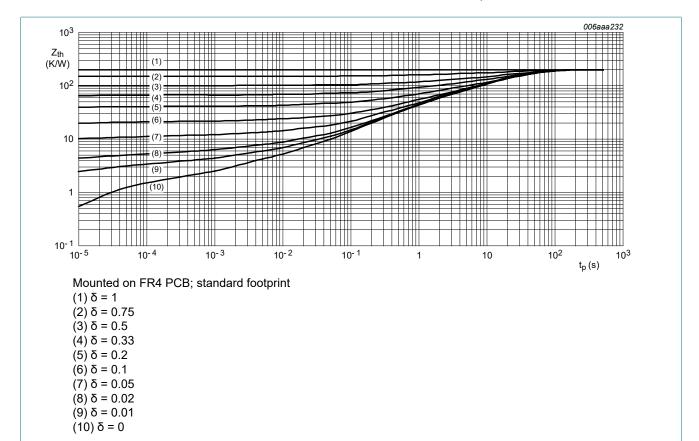
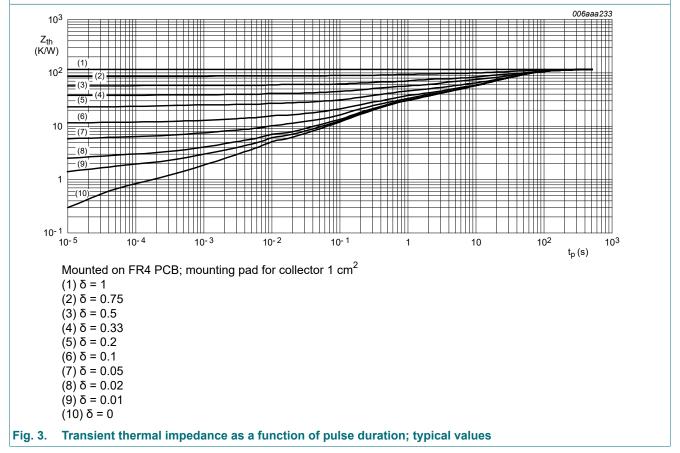
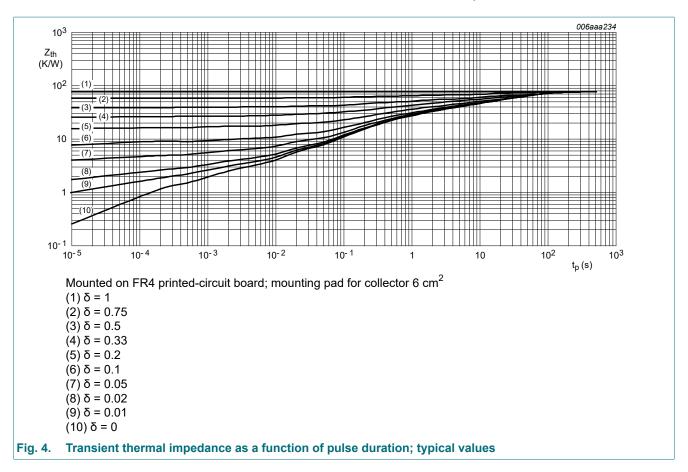


Fig. 2. Transient thermal impedance as a function of pulse duration; typical values



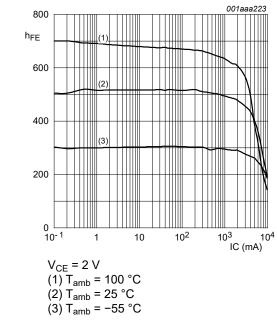


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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 30 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
current		V _{CB} = 30 V; I _E = 0 A; T _j = 150 °C	-	-	50	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
I _{CES}	collector-emitter cut-off current	V _{CE} = 30 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 2 V; I _C = 0.5 A; T _{amb} = 25 °C	300	-	-	
		V_{CE} = 2 V; I_{C} = 1 A; pulsed; $t_{p} \le 300 \ \mu s$; δ ≤ 0.02; T_{amb} = 25 °C	300	-	-	
		V_{CE} = 2 V; I_{C} = 2 A; pulsed; $t_{p} \le 300 \ \mu s$; δ ≤ 0.02; T_{amb} = 25 °C	250	-	-	
		V_{CE} = 2 V; I_{C} = 5 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	100	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 0.5 \text{ A}; I_B = 5 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	90	mV
		I _C = 1 A; I _B = 10 mA; T _{amb} = 25 °C	-	-	120	mV
		I_C = 2 A; I_B = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	150	mV
		I_C = 4 A; I_B = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	290	mV
		I_C = 5 A; I_B = 500 mA; pulsed; $t_p \le$	-	-	355	mV
R _{CEsat}	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	40	71	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = 4 A; I_B = 200 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	1.1	V
		I_C = 5 A; I_B = 500 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	1.2	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I_{C} = 2 A; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	1.1	V
fт	transition frequency	$V_{CE} = 10 \text{ V}; I_{C} = 0.1 \text{ A}; f = 100 \text{ MHz};$ $T_{amb} = 25 \text{ °C}$	70	-	-	MHz
C _c	collector capacitance	V_{CB} = 10 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	-	75	pF



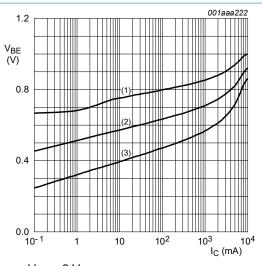
$$V_{CE} = 2 V$$

$$(1) T_{amb} = 100 ° ($$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 5. DC current gain as a function of collector current; typical values

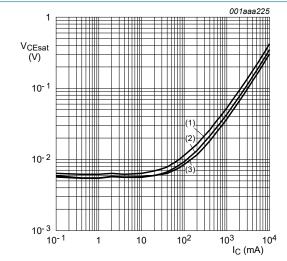


$$V_{CF} = 2 V$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = 100 °C$$

Fig. 6. Base-emitter voltage as a function of collector current; typical values



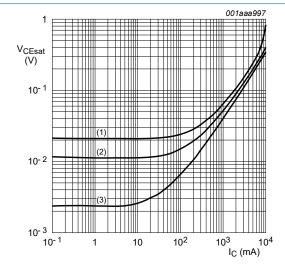
$$I_{\rm C}/I_{\rm B}=20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

$$(2) T_{amb} = 25 °C$$

$$(3) T_{amb} = -55 °C$$

Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values



$$(1) I_{\rm C}/I_{\rm B} = 100$$

(2)
$$I_C/I_B = 50$$

(3)
$$I_C/I_B = 10$$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

10²

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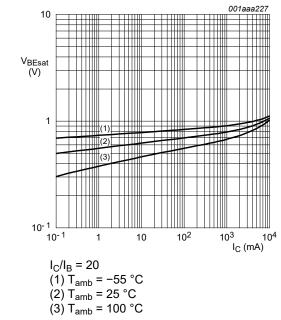
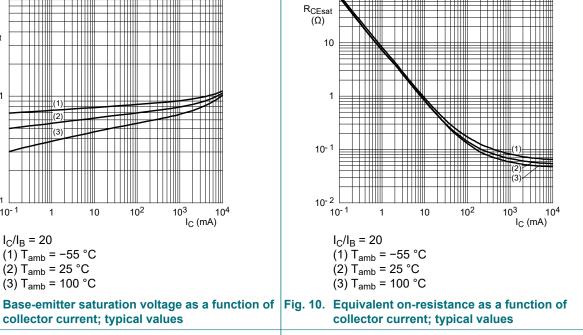
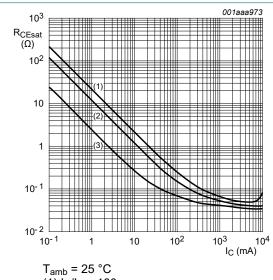


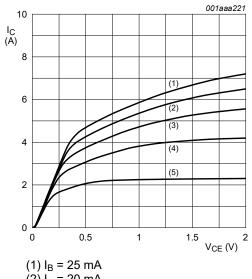
Fig. 9. collector current; typical values





(1) $I_C/I_B = 100$ (2) $I_C/I_B = 50$ $(3) I_{\rm C}/I_{\rm B} = 10$

Fig. 11. Equivalent on-resistance as a function of collector current; typical values



(2) $I_B = 20 \text{ mA}$ (3) $I_B = 15 \text{ mA}$

 $(4) I_B = 10 mA$ (5) $I_B = 5 \text{ mA}$

Fig. 12. Collector current as a function of collectoremitter voltage; typical values

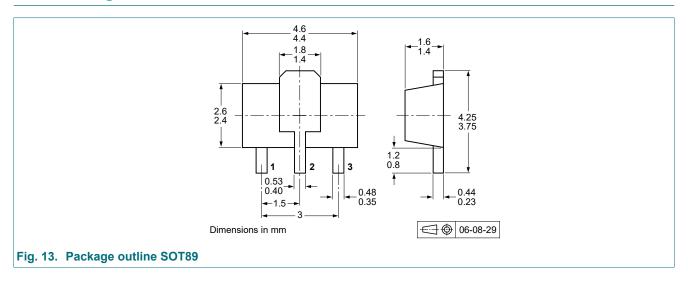
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11. Test information

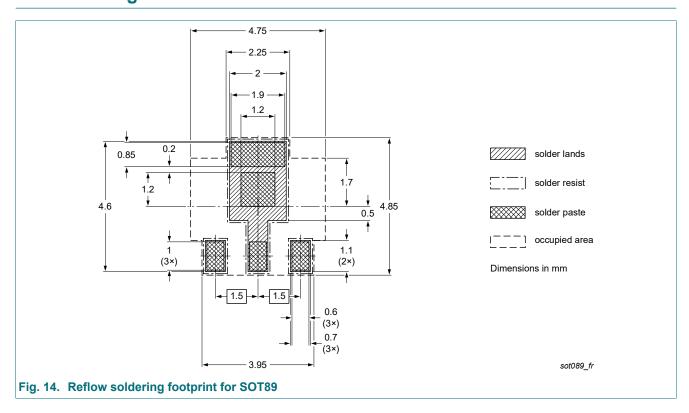
Quality information

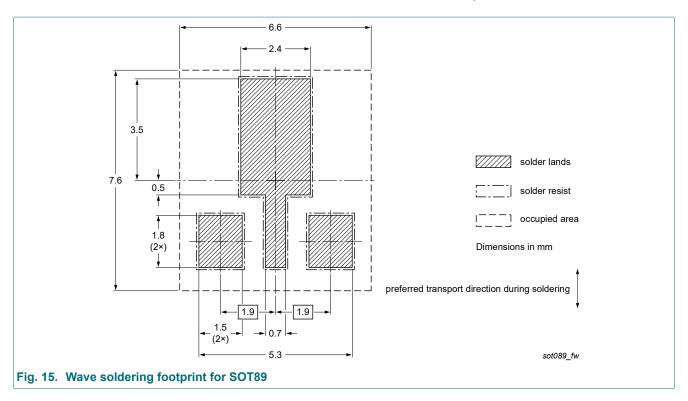
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



13. Soldering





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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4540X-Q v.1	20240122	Product data sheet	-	-

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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